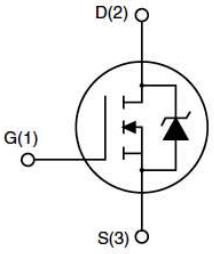
ZHEJIANG UNIU-NE Technology CO.,LTD

浙 江 宇 力 微 新 能 源 科 技 有 限 公 司

APG038N01G Data Sheet

V 1.1

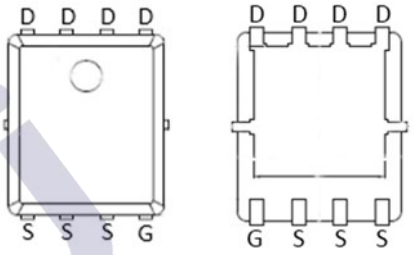
Feature



- 100V,104A
  $R_{DS(ON)}$ <3.8mΩ @V_{GS}=10V (TYP:3.1mΩ)
  $R_{DS(ON)}$ <4.9mΩ @V_{GS}=4.5V (TYP:4.2mΩ)
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge

Application

- PWM applications
- Load Switch
- Power management



PDFN5X6

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G038N01G	APG038N01G	PDFN5X6	-	-	5000

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (T_a =25℃)	I_D	104	A
Continuous Drain Current (T_a =100℃)	I_D	65.7	A
Pulsed Drain Currenr (1)	I_{DM}	416	A
Single Pulsed Avalanche Energy (2)	E_{AS}	324	mJ
Power Dissipation	P_D	67.5	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.85	℃/W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	51.4	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	100	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} =100V, V_{GS} = 0V	-	-	1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage(3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1.5	2.0	3.0	V
Drain-source on-resistance(3)	$R_{DS(on)}$	V_{GS} =10V, I_D =30A	-	3.1	3.8	mΩ
		V_{GS} =4.5V, I_D =20A	-	4.2	4.9	mΩ
Gate Resistance	R_g	V_{DS} =V_{GS} =0V, f =1MHz	-	1.7	-	Ω
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =50V, V_{GS} =0V, f =1MHz	-	5980	-	pF
Output Capacitance	C_{oss}		-	1270	-	
Reverse Transfer Capacitance	C_{rss}		-	31.5	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{DD}=50V, I_D=20A, V_{GS}=10V, R_G=3Ω	-	23.5	-	ns
Turn-on rise time	t_r		-	33.6	-	
Turn-off delay time	$t_{d(off)}$		-	89	-	
Turn-off fall time	t_f		-	25.7	-	
Total Gate Charge	Qg	VDS=50V, ID=20A, VGS=10V	-	100	-	nC
Gate-Source Charge	Qgs		-	17	-	
Gate-Drain Charge	Qgd		-	20.7	-	
Reverse Recovery Chrage	Qrr	I_F=80A,di/dt=100A/us		103.8		nC
Reverse Recovery Time	Trr	I_F=80A,di/dt=100A/us		62.6		ns
Source-Drain Diode characteristics						
Diode Forward voltage(3)	V_{DS}	V_{GS} =0V, I_S=40A	-	0.85	1.3	V
Diode Forward current(4)	I_S		-	-	104	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition:T_J=25℃,V_{DD}=50V,R_G=25Ω,L=0.5Mh,IAS=36A
3. Pulse Test: pulse width≤300μs, duty cycle≤2%
4. Surface Mounted on FR4 Board,t≤10 sec

■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

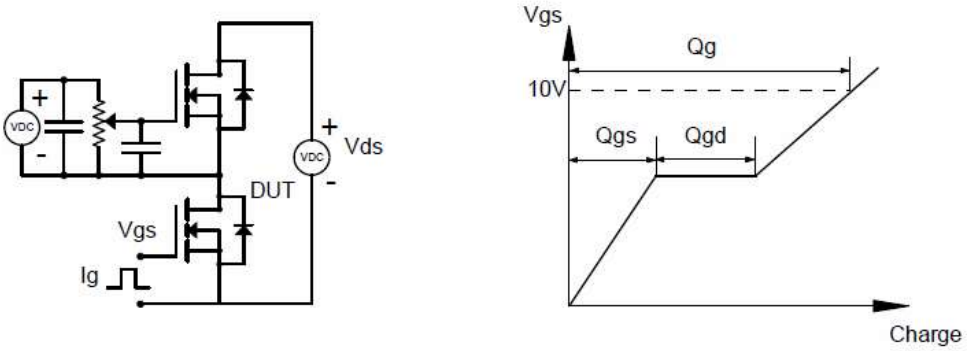


Figure B: Resistive Switching Test Circuit & Waveforms

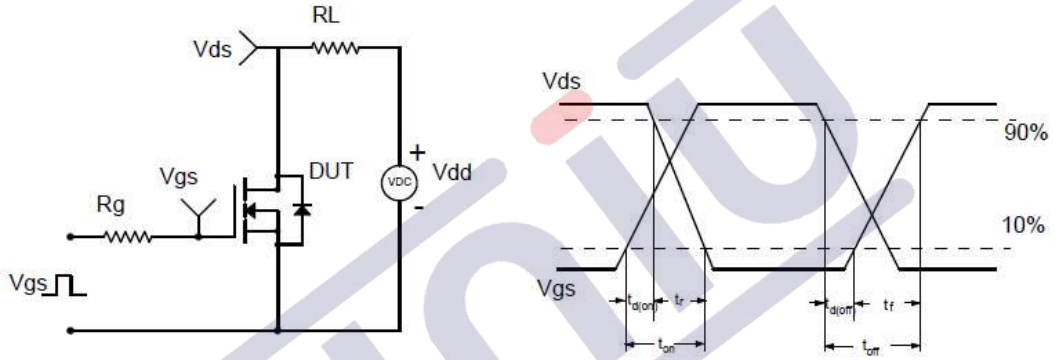


Figure C: Unclamped Inductive Switching (UIS) Test

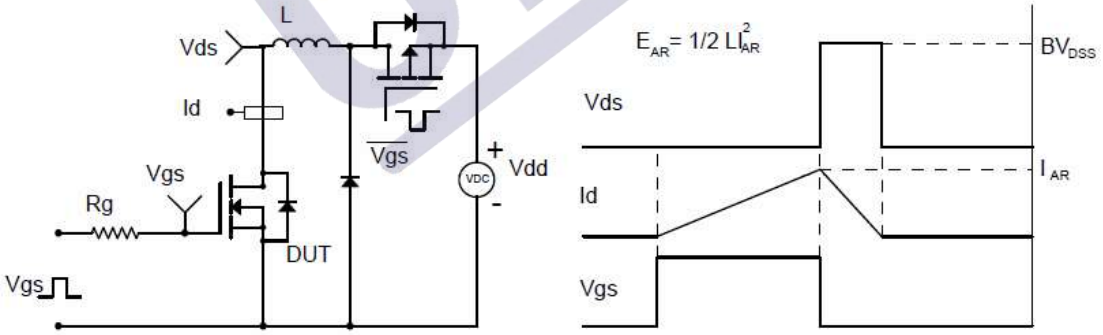
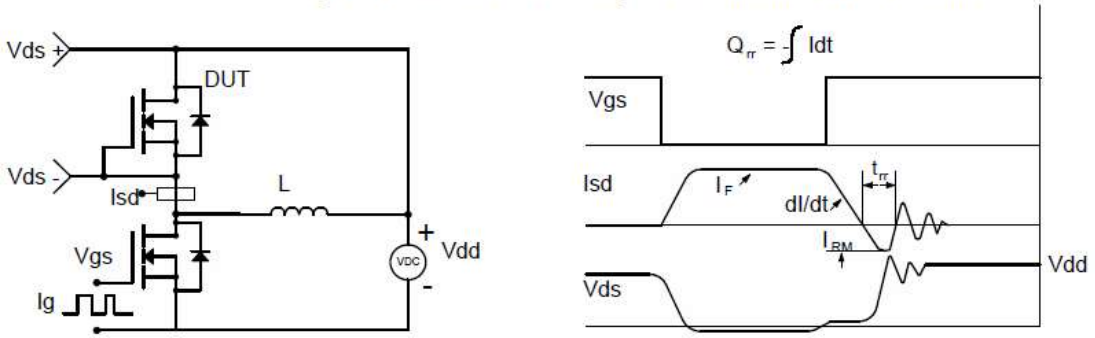


Figure D: Diode Recovery Test Circuit & Waveforms



Typical Electronic and Thermal Characteristics

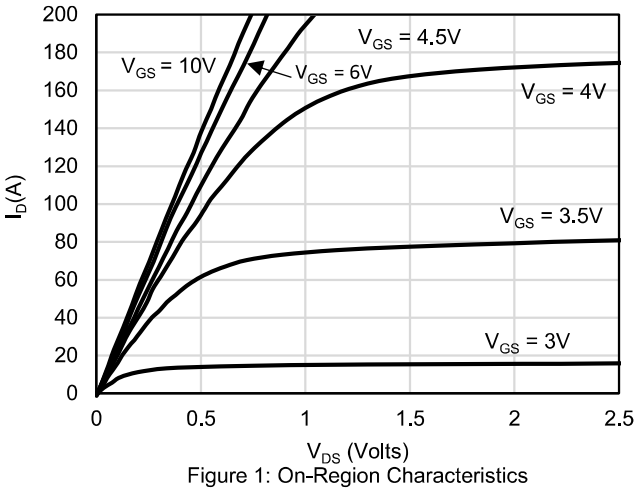


Figure 1: On-Region Characteristics

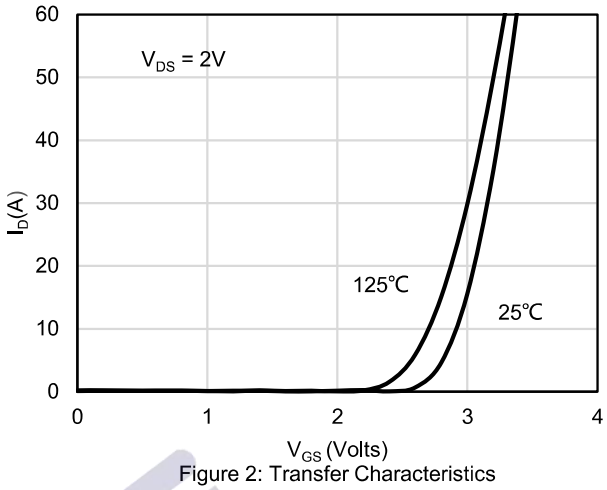


Figure 2: Transfer Characteristics

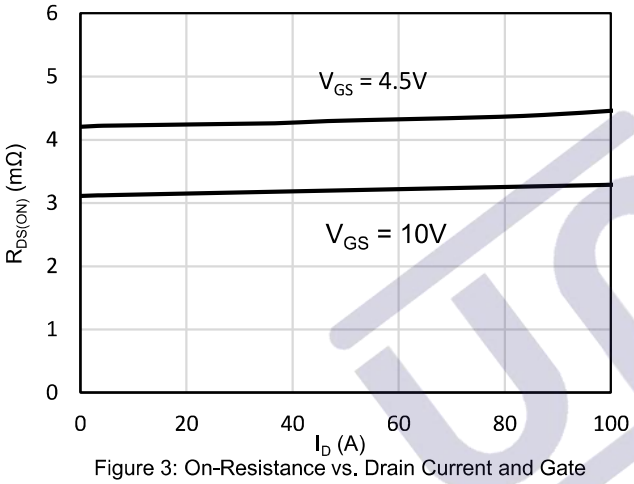


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

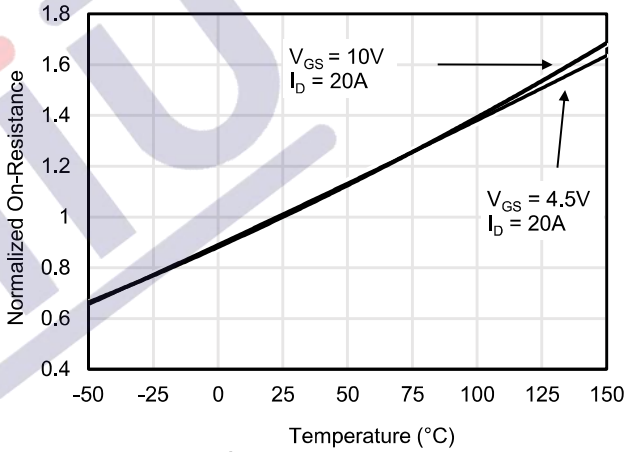


Figure 4: On-Resistance vs. Junction Temperature

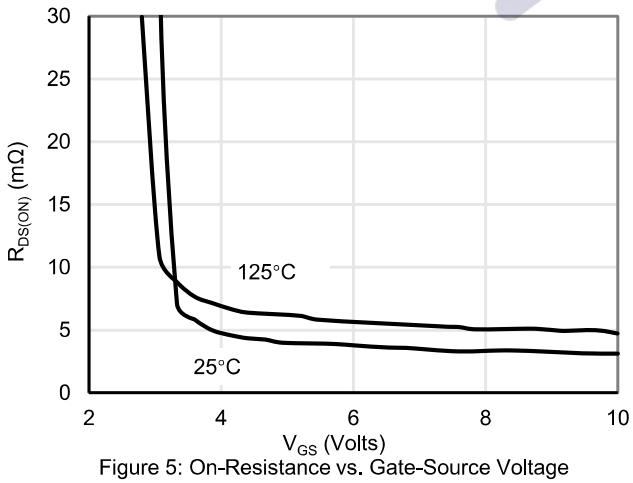


Figure 5: On-Resistance vs. Gate-Source Voltage

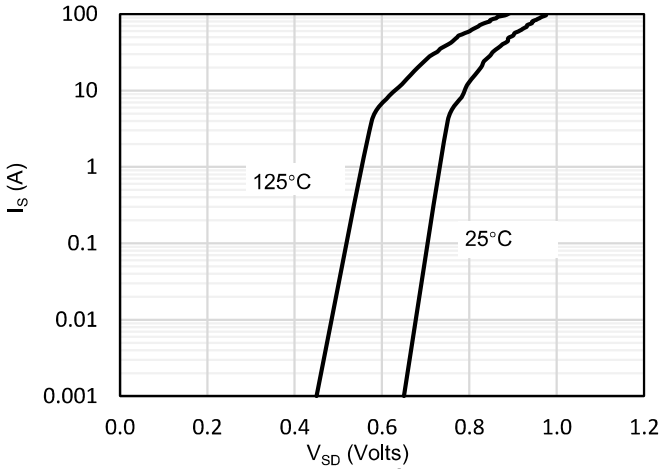


Figure 6: Body-Diode Characteristics

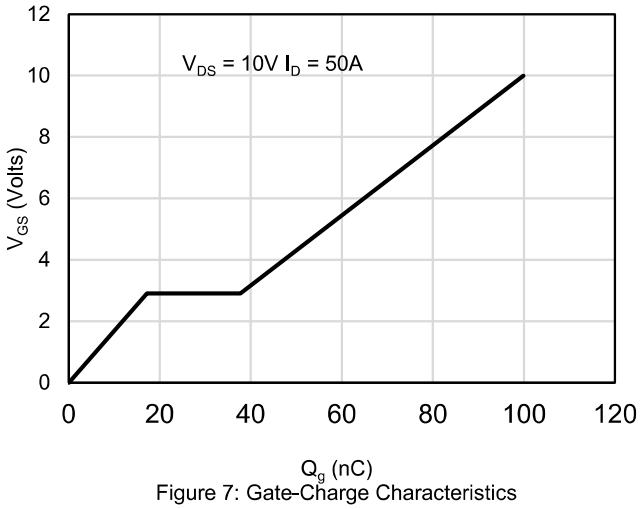


Figure 7: Gate-Charge Characteristics

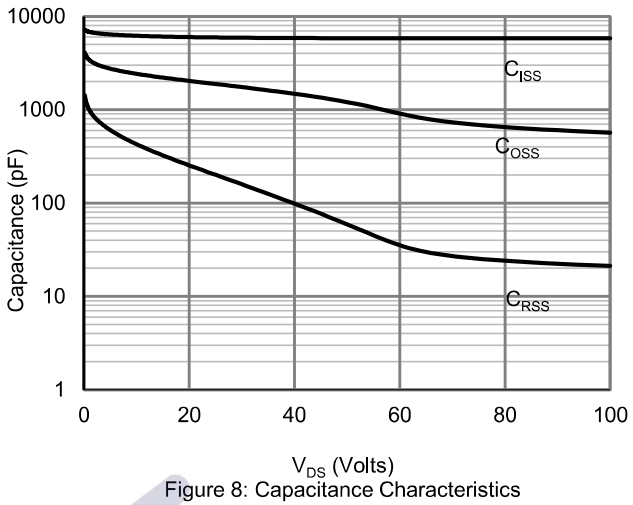


Figure 8: Capacitance Characteristics

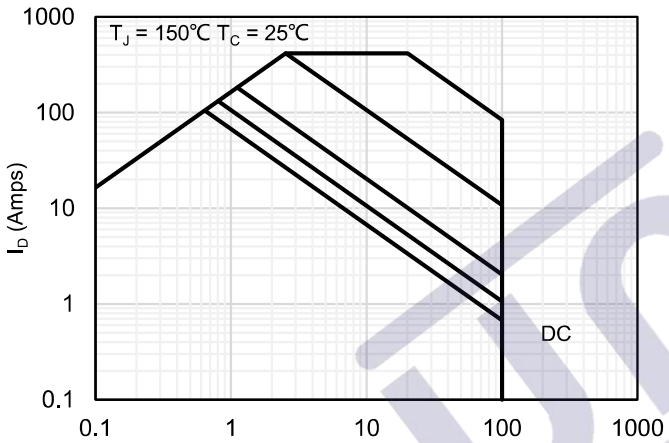


Figure 9: Maximum Forward Biased Safe Operating Area

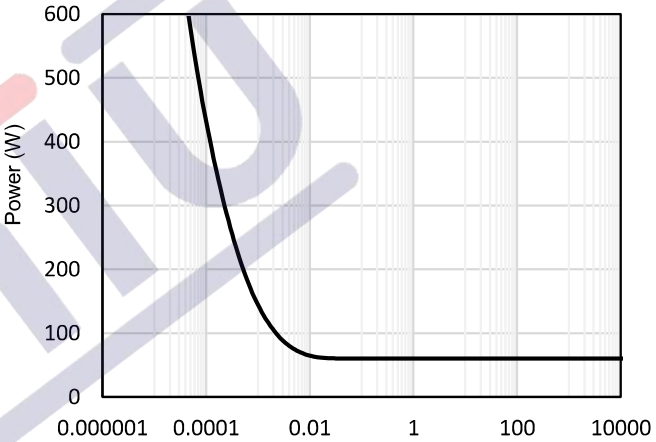


Figure 10: Single Pulse Power Rating Junction-to-Case

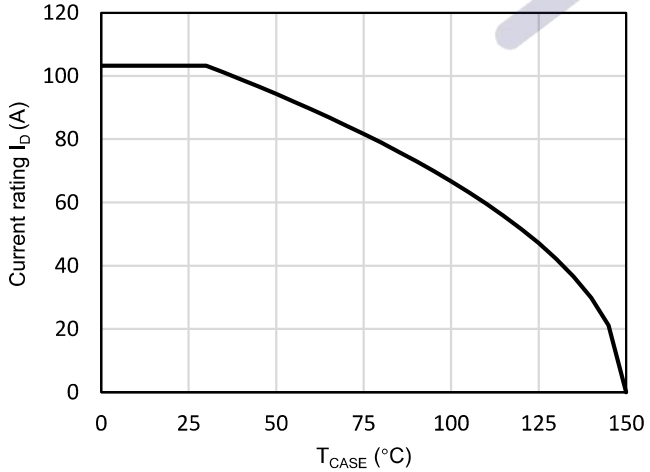


Figure 11: Current De-rating

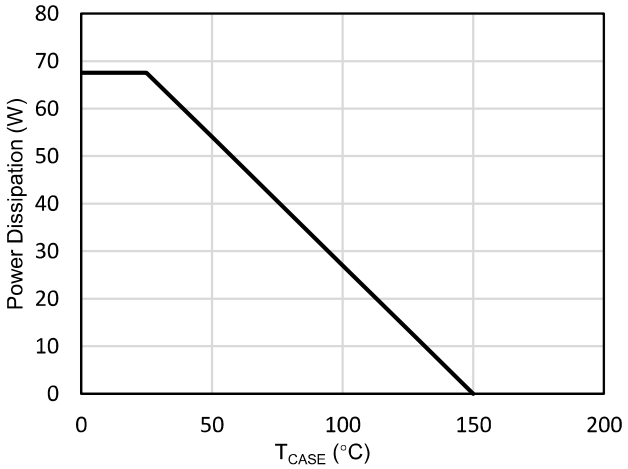


Figure 12: Power De-rating

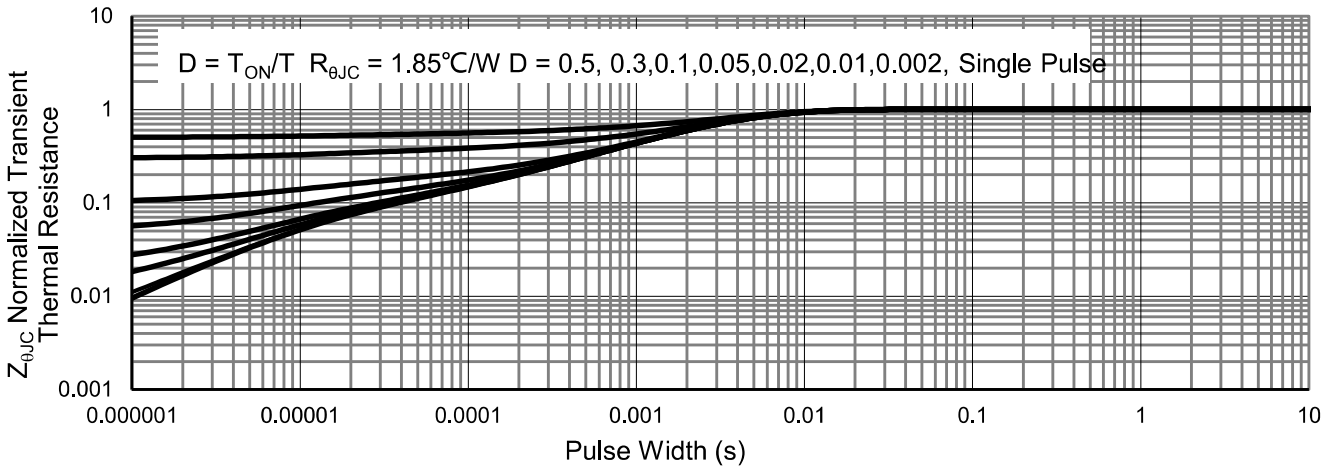
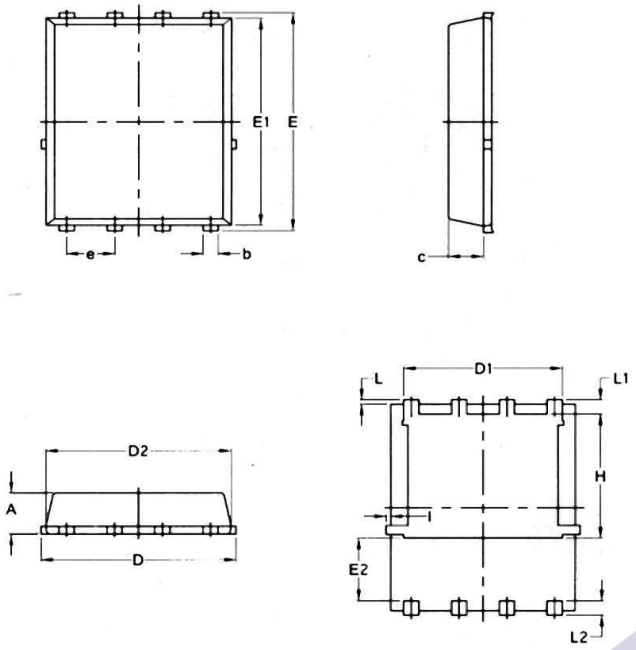


Figure 13: Normalized Maximum Transient Thermal Impedance

PDFN5X6 Package Information



PDFN5X6

SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	—	0.0630	—
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	—	0.18	—	0.0070

1.版本记录

DATE	REV.	DESCRIPTION
2018/11/15	1.0	First Release
2020/09/18	1.1	Layout adjustment

2.免责声明

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3.联系我们

浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渎路25号中节能科创园45幢4/5楼
电话：0575-85087896（研发部）
传真：0575-88125157
E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路 6 号中国电子（无锡）数字芯城 1#综合楼 503室
电 话 : 0510-85297939
E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410
电 话 ： 0755-84510976
E-mail: htw@uni-semic.com